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Form PTO-1449 Modified List of Patents and Publications Cited by Applicant (Use several sheets if necessary) U.S. Patent Department of Commerce Patent and Trademark Office	Docket No.: 20661-801D1	Serial No.: 09/964,192
	Applicants: Varun Singh, et al.	COPY OF PAPERS ORIGINALLY FILED
	Filing Date: 9/26/01	Group: 2812

U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Date	Name	Class	Subclass
EL	A-1	4,210,996	7/08/1980	Amemiya et al.	29	610
EL	A-2	5,187,559	2/16/1993	Isobe et al.	257	538
EL	A-3	5,854,103	12/29/1998	Liang	438	238
EL	A-4	6,204,105	3/20/2001	Jung	438	238

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FOREIGN PATENT DOCUMENTS

Examiner Initial		Document No.	Date	Country	Translation	
					Yes	No
	B-1					

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OTHER DOCUMENTS

Examiner Initials		Author, Title, Date, Pertinent Pages, Etc.
	C-1	"Electrical Trimming of Heavily Doped Polycrystalline Silicon Resistors", by Yoshihito Amemiya, Terukazu Ono and Kotaro Kato, IEEE Transactions on Electron Devices, Vol. ED-26, No. 11, November 1979
	C-2	"A Physical Mechanism of Current-Induced Resistance Decrease in Heavily Doped Polysilicon Resistors", by Kotaro Kato, Terukazu Ono, and Yoshihito Amemiya, IEEE Transactions on Electron Devices, Vol. ED-29, No. 8, August 1982
	C-3	"A Monolithic 14 Bit D/A Converter Fabricated with a New Trimming Technique (DOT)", by Kotaro Kato, Terukazu Ono, and Yoshihito Amemiya, IEEE Journal of Solid-State Circuits, Vol. SC-19, No. 5, October 1984
	C-4	"Polysilicon Resistor Trimming for Packaged Integrated Circuits", by J.A. Babcock, D.W. Feldbaumer, and V.M. Mercier, IEEE, 1993
	C-5	"ElectricalTrimming of Ion-Beam-Sputtered Polysilicon Resistors by High Current Pulses", by Soumen Das and Samir K. Lahiri, IEEE Transactions on Electron Devices, Vol. 41, No. 8, August 1994
	C-6	"Constant Voltage Trimming of Heavily Doped Polysilicon Resistors", by Kotaro Kato and Terukazu Ono, Jpn. J. Appl. Phys. Vol. 34, pp. 48-53, January 1995
	C-7	"Theory and Application of Polysilicon Resistor Trimming", by D.W. Feldbaumer and J.A. Babcock, Solid-State Electronics Vol. 38, No. 11, pp. 1861 - 1869, 1995
	C-8	"Pulse Current Trimming of Polysilicon Resistors", by David W. Feldbaumer, Jeffrey A. Babcock, Vickie M. Mercier, and Christopher K.Y. Chun, IEEE Transactions on Electron Devices, Vol. 42, No. 4, April 1995
	C-9	"Change in Temperature Coefficient of Resistance of Heavily Doped Polysilicon Resistors Caused by Electrical Trimming", by Kotaro Kato and Terukazu Ono, Jpn. J. Appl. Phys. Vol. 35, pp. 4209-4215, August 1996
	C-10	"Polycrystalline Silicon for Integrated Circuits and Displays Second Edition", by Ted Kamins, P. 266, 1998

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Date Examined: 6/12/02	**Examiner:**